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November 2013

FQT2P25

P-Channel QFET® MOSFET

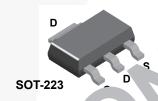
-250 V, -0.55 A, 4.0 Ω

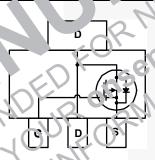
Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize onstate resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters.

Features

- -0.55 A, -250 V, R_{DS(on)} = 4.0 Ω (Max.) @ V_{GS} = -10 V, I_D = -0.275 A
- Low Gate Charge (Typ. 6.5 nC)
- Low Crss (Typ. 6.5 pF)
- · 100% Avalanche Tested





Absolute May num Ra....gs Tc = 15°C unless otherwise noted.

Symbol	Parametor		FQT2P25TF	Unit
V _{DS}	Source voltage		-250	V
$\overline{I_D}$	Drain urrent • Continuous (1°C = 25°C)		-0.55	Α
	Continuous ($T_C = 100^{\circ}$ C)	\ `	-0.35	Α
I _{DM}	Drain Curre it - Pulsed	(Note 1)	-2.2	Α
V _G e	Gata-Source Voltage		± 30	V
าร	Single Puiced Avalanche Energy	(Note 2)	120	mJ
I _{AR}	Avalanche Current	(Note 1)	-0.55	А
EAR	Repetitive Avalancine Energy	(Note 1)	0.25	mJ
c'v/dt	Peak Dipde L'ecovery dv/dt (Note 3)		-5.5	V/ns
P _D	Pov.er Dissipation (T _C = 25°C)		2.5	W
	- Derate above 25°C		0.02	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQT2P25TF	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	50	°C/W

^{*} When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQT2P25TF	FQT2P25	SOT-223	Tape and Reel	13 "	12 mm	4000 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Parameter	Test Conditions	Min	Тур	Max	Unit
racteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-250			V
Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.2		V/°C
Zero Gate Voltage Drain Current	V _{DS} = -250 V, V _{GS} = 0 V V _{DS} = -200 V, T _C = 125°C			-1ι	μA μA
Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			J	112
	Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250$ A	.05.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _L 275	315 4.0	Ω
9 _{FS}	Forward Transconductance	V_{DS} ,0 \ $=$ 275 A	- 0.6	8

Dynamic Characteristics

C _{iss}	Input Capacitance	$rac{1}{1}$ $rac{1}$ $rac{1}{1}$ $rac{1}$ $rac{1}{1}$ $rac{1}{1}$ $rac{1}$ $rac{1}$ $rac{1}{1}$ $rac{1}$ $rac{$	pF
Coss	Output Capacitance	1.0 MHz 40 55	pF
C _{rss}	Reverse Transfer Car Litanic	-() 6.5 8.5	pF

Switching Charac

$t_{d(on)}$	Turn-On [lay Time $V_{DD} = -125 \text{ V}, I_D = -2.3 \text{ A},$		8.5	25	ns
t _r	T in R Time $V_{DD} = -125 \text{ V, i}_{D} = -13 \text{ A},$ $R_G = 25 \Omega$		40	90	ns
t _{d(off)}	urn-0" Dela,		12	35	ns
t _f	rum-Off II Time (Note 4)		25	60	ns
	To e Charg : $V_{DS} = -200 \text{ V}, I_{D} = -2.3 \text{ A},$		6.5	8.5	nC
Q _{gs}	nte-Source Cinarge \(\frac{1}{GS} = -10 \text{ V}	/	1.8		nC
Q _{gd}	Gate Drain Charge (Note 4)		3.0		nC

Drain-Source Diode Characteristics and Maximum Ratings

5	Maximum Continuous Diain-Source Diode Forward Current		 -	-0.55	Α
IgM	Maximum Pulse i Drain-Source Diode Forward Current		 -	-2.2	Α
V _{SD}	Drain-Spurce Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -0.55 \text{ A}$	 	-5.0	V
trr	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = -2.3 \text{ A},$	 110	//	ns
Qrr	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$	 0.4		μC

- 1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 635 mH, I_{AS} = -0.55 A, V_{DD} = -50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} ≤ -2.3 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C.
- 4. Essentially independent of operating temperature.

Typical Characteristics

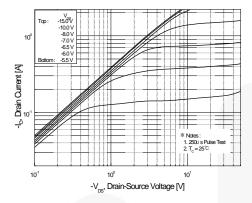


Figure 1. On-Region Characteristics

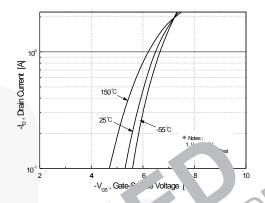
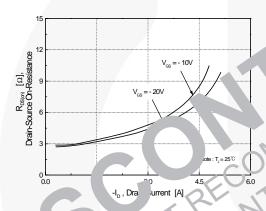


Figure 2. 1 nst. Che steristics



rigure 3 On-Resistance Variation vs Current and Gate Voltage

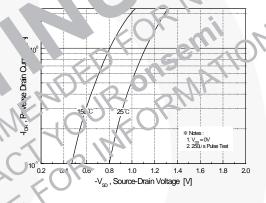


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

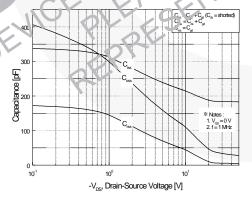


Figure 5. Capacitance Characteristics

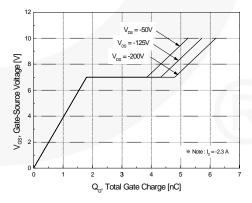


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

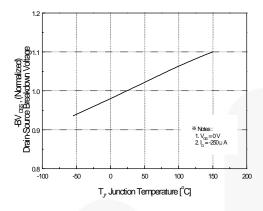
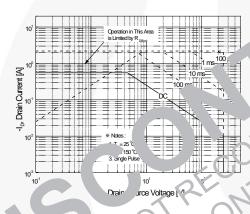


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. Re tance ariation vs. mp are



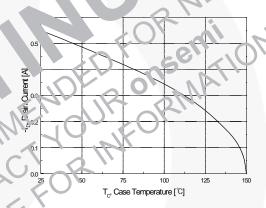


Figure 9. aximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

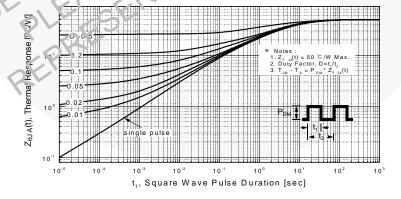


Figure 11. Transient Thermal Response Curve

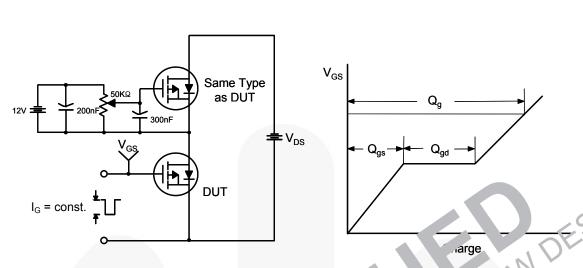


Figure 12. Gate Charge Test Circuit & Vave. m

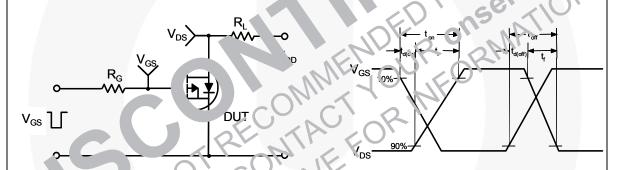


Figure 13. Resistive Switching Test Circuit & Waveforms

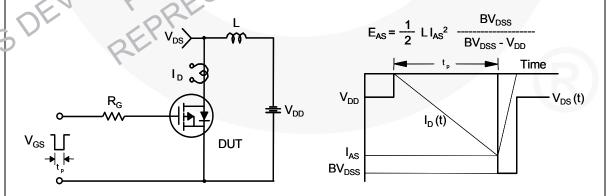
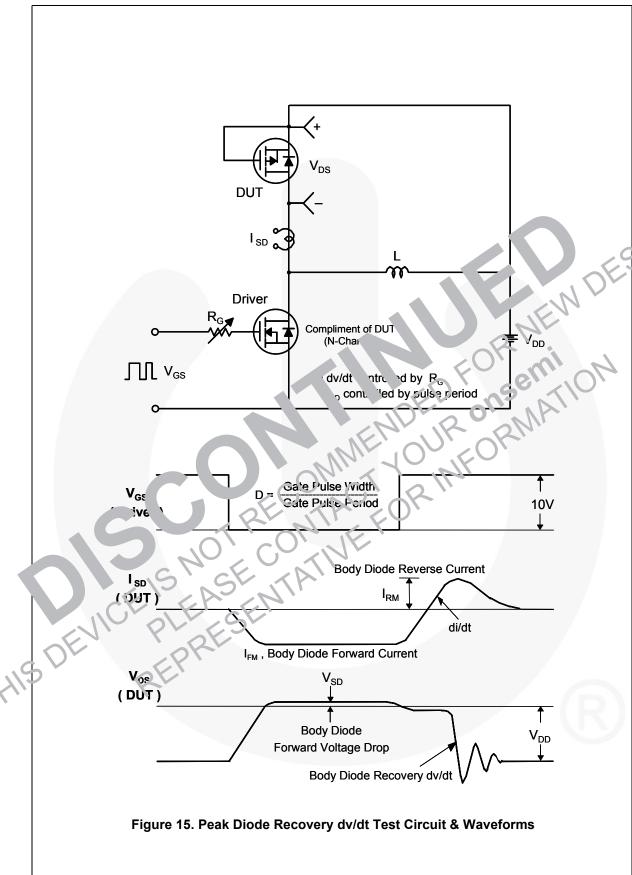


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

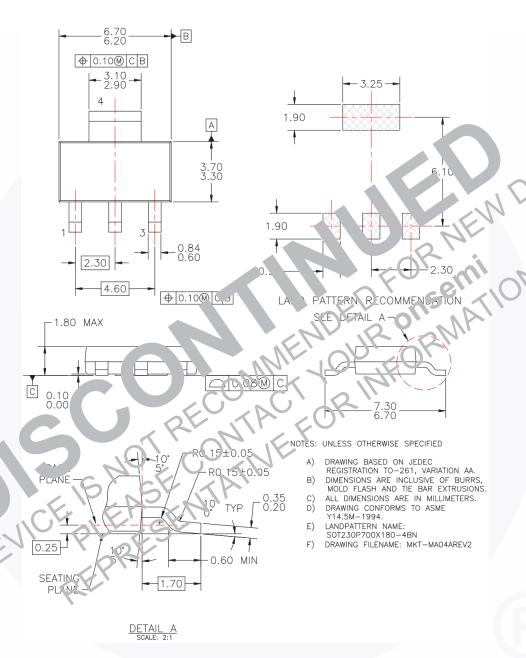


Figure 16. SOT-223, Molded, 4-Lead

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